Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S5	111	(257/059 or 257/72 or 257/765 or 257/771).ccls. and ((gate or drain or source or electrode) same ((aluminum or al) and (titanium or ti) and (titanium adj nitride) and (TiN)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/20 19:45
S6	90	(257/059 or 257/72 or 257/765 or 257/771).ccls. and ((gate or drain or source or electrode) same ((aluminum or al) and (titanium or ti) and (titanium adj nitride) and (TiN))) and @ad<"20030312"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/20 23:39
S7	155	(349/139 or 349/147 or 349/148). ccls. and ((gate or drain or source or electrode) same ((aluminum or al) and (titanium or ti) and ((titanium adj nitride) or (TiN)))) and @ad<"20030312"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 00:03
S10	8877	(semiconductor or TFT) and ((gate or drain or source or electrode) same ((aluminum or al) and (titanium or ti) and ((titanium adj nitride) or (TiN)))) and @ad<"20030312"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 00:04
S11	4731	(semiconductor or TFT or display) and ((gate or drain or source or electrode) with ((aluminum or al) and (titanium or ti) and ((titanium adj nitride) or (TiN)))) and @ad<"20030312"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 00:05
S12	0	(semiconductor or TFT or display) and ((gate or drain or source or electrode) with (Ti/TiN/Al/TiN/Ti)) and @ad<"20030312"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 00:07
S13	0	(semiconductor or TFT or display) and ((gate or drain or source or electrode) same (Ti/TiN/AI/TiN/Ti)) and @ad<"20030312"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 00:07
S14	2213	(semiconductor or TFT or display) and ((gate or drain or source or electrode) with (Ti and TiN and (Al or Aluminum))) and @ad<"20030312"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 00:36

S15	185	(semiconductor or TFT or display) and ((gate or drain or source or electrode) with (Ti and TiN and (Al or Aluminum))) and @ad<"20030312" and ((diffusion near5 (preven\$5 or barrier)) with (TiN or (titanium adj nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 00:38
S16	20	(semiconductor or TFT or display) and (((gate or drain or source or electrode) with (Ti and TiN and (Al or Aluminum))) same ((diffusion near5 (preven\$5 or barrier)) with (TiN or (titanium adj nitride)))) and @ad<"20030312"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 01:30
S17	660	(semiconductor or TFT or display) and ((gate or drain or source or electrode) with (Ti and TiN and (Al or Aluminum))) and @ad<"20030312" and ((preven\$5 or barrier) with (TiN or (titanium adj nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 00:39
S18	475	(semiconductor or TFT or display) and ((gate or drain or source or electrode) with (Ti and TiN and (Al or Aluminum))) and @ad<"20030312" and ((preven\$5 or barrier) with (TiN or (titanium adj nitride))) not S15	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR ·	ON	2005/06/21 10:30
S20	741	(semiconductor or TFT or display or LCD) and ((gate or drain or source or electrode) with (Ti and TiN and (Al or Aluminum))) and @ad<"20030312" and ((drain near3 electrode) with (gate near3 electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 10:38
S21	510	(TFT or display or LCD) and ((gate or drain or source or electrode) with (Ti and TiN and (Al or Aluminum))) and @ad<"20030312" and ((drain near3 electrode) with (gate near3 electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 10:43
S22	828	(TFT or display or LCD) and ((gate or drain or source or electrode) with ((titanium or Ti) and (titanium adj nitride or TiN) and (Al or Aluminum))) and @ad<"20030312" and ((drain near3 electrode) with (gate near3 electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/21 10:46